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1. Global joint venture starts operations as WeEn Semiconductors

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In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





1. General description

Planar passivated four quadrant triac in a SOT428 (DPAK) surface-mountable plastic package intended for use in general purpose bidirectional and phase control applications.

2. Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants

3. Applications

- General purpose motor controls
- General purpose switching

4. Quick reference data

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	4	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4; Fig. 5</u>	-	-	25	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ t _p = 16.7 ms	-	-	27	A
Tj	junction temperature		-	-	125	°C
Static chara	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	5	25	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	8	25	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	11	25	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _i = 25 °C; <u>Fig. 7</u>	-	30	70	mA

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>		-	5	15	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>		-	1.4	1.7	V
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		50	250	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_{D} = 400 V; T_{j} = 95 °C; dI_{com}/dt = 1.8 A/ ms; I_T = 4 A; gate open circuit		-	50	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2T1
2	T2	main terminal 2		sym051
3	G	gate		Symuon
mb	Τ2	mounting base; main terminal 2	DPAK (SOT428)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BT136S-800F	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			



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7. Limiting values

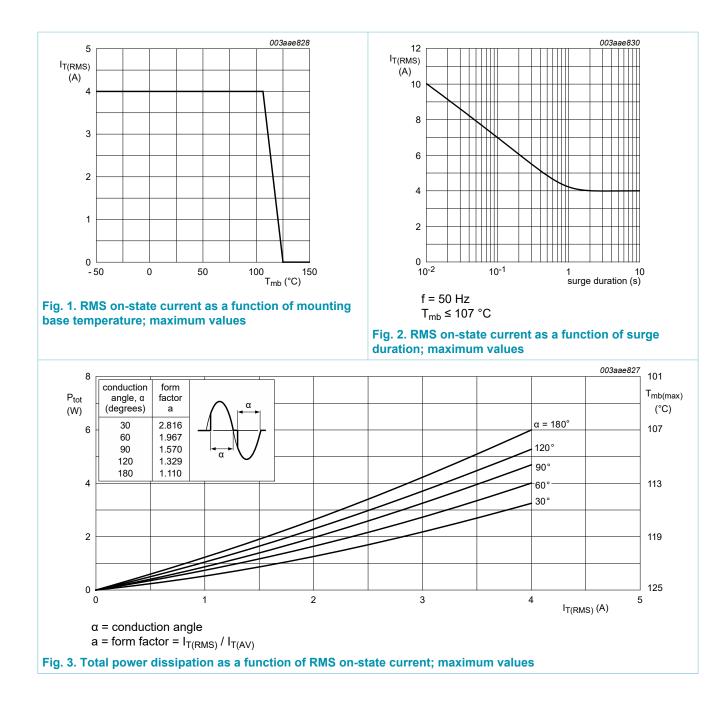
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	4	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4; Fig. 5</u>	-	25	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	27	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	3.1	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	50	A/µs
			-	50	A/µs
		I _G = 70 mA	-	50	A/µs
		I _G = 0.2 A	-	50	A/µs
		I _G = 70 mA	-	50	A/µs
		I _G = 0.2 A	-	10	A/µs
		I _G = 140 mA	-	10	A/µs
		I _G = 70 mA	-	50	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

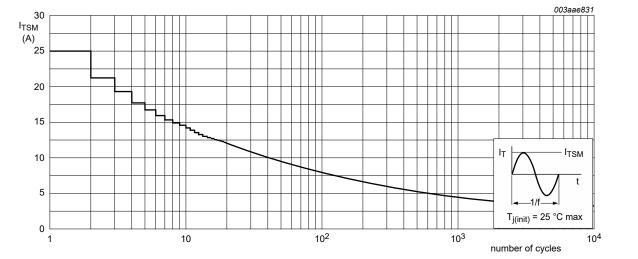
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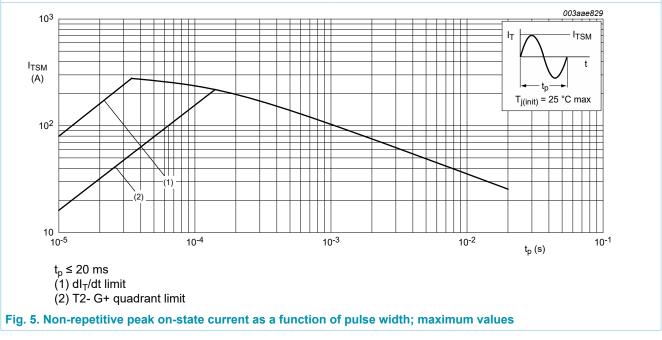
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f = 50 Hz



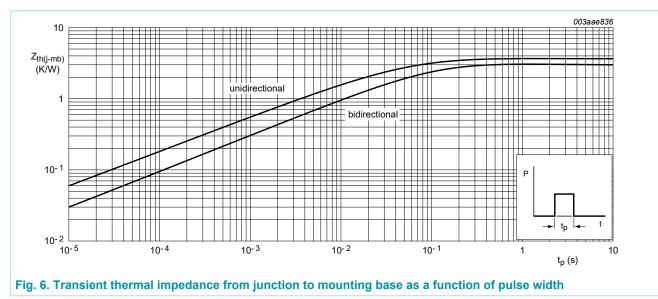




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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	3.7	K/W
		full cycle; <u>Fig. 6</u>	-	-	3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air; printed circuit board (FR4) mounted; standard footprint, single- sided copper, tin-plated	-	75	-	K/W





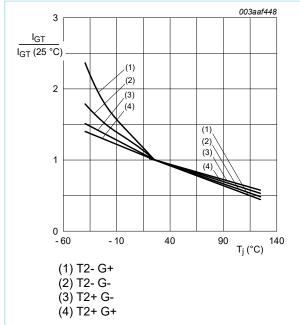
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9. Characteristics

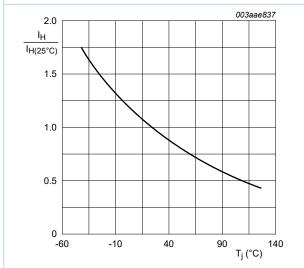
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·				
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	5	25	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	8	25	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	11	25	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	30	70	mA
ΙL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	7	20	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	16	30	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	5	20	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 8</u>	-	7	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	5	15	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 11</u>	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; <u>Fig. 11</u>	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	50	250	-	V/µs
dV _{com} /dt	rate of change of commutating voltage			50	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 6 A; V_D = 800 V; I_G = 0.1 mA; d I_G / dt = 5 A/µs	-	2	-	μs

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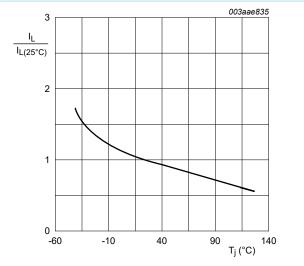
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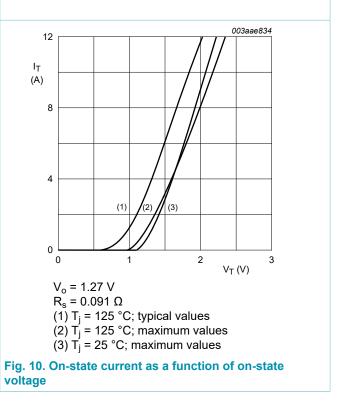






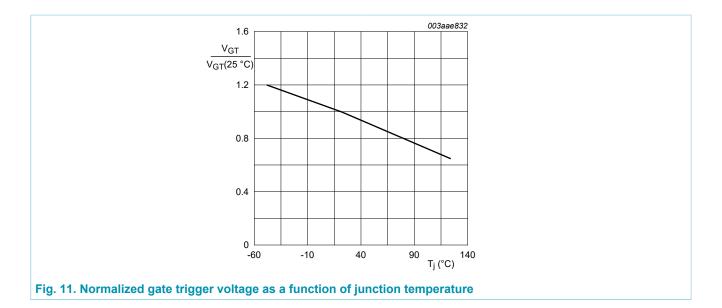






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10. Package outline

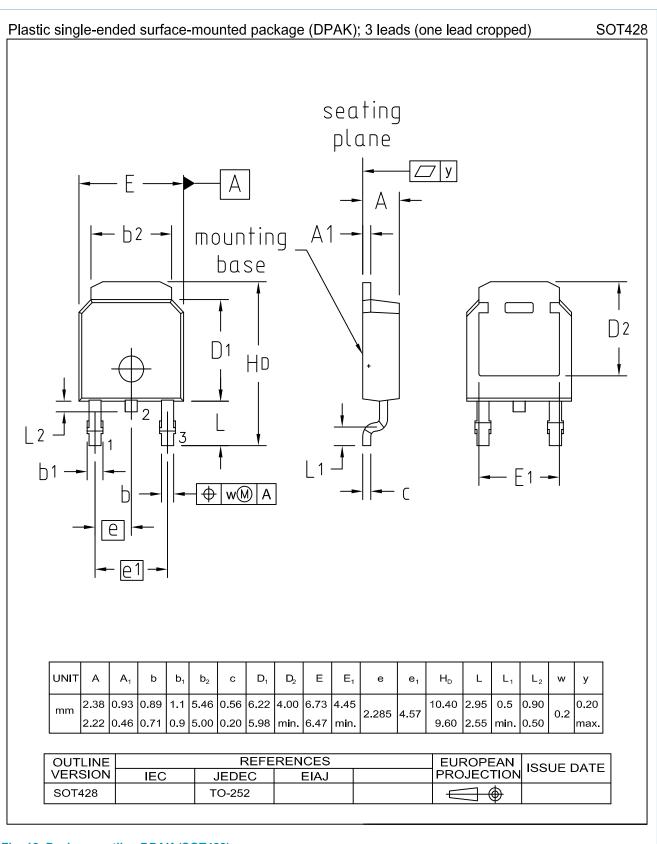


Fig. 12. Package outline DPAK (SOT428)
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11. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.ween-semi.com</u>.

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